500 mW DO-35 Hermetically Sealed Glass Zener Voltage Regulators

This is a complete series of 500 mW Zener diodes with limits and excellent operating characteristics that reflect the superior capabilities of silicon—oxide passivated junctions. All this in an axial—lead hermetically sealed glass package that offers protection in all common environmental conditions.

Specification Features:

- Zener Voltage Range 6.8 V to 75 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- DO-204AH (DO-35) Package Smaller than Conventional DO-204AA Package
- Double Slug Type Construction
- Metallurgical Bonded Construction

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass

FINISH: All external surfaces are corrosion resistant and leads are

readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:

230°C, 1/16" from the case for 10 seconds **POLARITY:** Cathode indicated by polarity band

MOUNTING POSITION: Any

MAXIMUM RATINGS (Note 1.)

Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ T _L ≤ 75°C, Lead Length = 3/8″	P _D	500	mW
Derate above 75°C		4.0	mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	–65 to +200	°C

1. Some part number series have lower JEDEC registered ratings.



ON Semiconductor™

http://onsemi.com





MARKING DIAGRAM



L = Assembly Location

1N9xxB = Device Code

(See Table Next Page)

Y = Year WW = Work Week

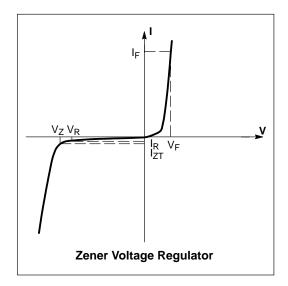
ORDERING INFORMATION

Device	Package	Shipping
1N9xxB	Axial Lead	3000 Units/Box
1N9xxBRL	Axial Lead	5000/Tape & Reel
1N9xxBRL2 *	Axial Lead	5000/Tape & Reel
1N9xxBRA1	Axial Lead	3000/Ammo Pack
1N9xxBTA	Axial Lead	5000/Ammo Pack
1N9xxBTA2 *	Axial Lead	5000/Tape & Reel
1N9xxBRR1 [†]	Axial Lead	3000/Tape & Reel
1N9xxBRR2 [‡]	Axial Lead	3000/Tape & Reel

- * The "2" suffix refers to 26 mm tape spacing.
- † Polarity band **up** with cathode lead off first
- [‡] Polarity band **down** with cathode lead off first

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 1.5$ V Max @ $I_F = 200$ mA for all types)

Symbol	Parameter					
VZ	Reverse Zener Voltage @ I _{ZT}					
I _{ZT}	Reverse Current					
Z _{ZT} Maximum Zener Impedance @ I _{ZT}						
I _{ZK}	Reverse Current					
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}					
I _R Reverse Leakage Current @ V _R						
V _R	Breakdown Voltage					
I _F Forward Current						
V _F	Forward Voltage @ I _F					
I _{ZM}	Maximum DC Zener Current					



ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted, $V_F = 1.5$ V Max @ $I_F = 200$ mA for all types)

Zener Voltage (Note 3.)			Zener Impedance (Note 4.)			Leakage Current		I _{ZM}			
Device	Device		V _Z (Volts)		@ l _{ZT}	Z _{ZT} @ I _{ZT}	Z _{ZK} (Z _{ZK} @ I _{ZK} I _R @		V _R	(Note 5.)
(Note 2.)	Marking	Min	Nom	Max	mA	Ω	Ω	mA	μ Α	Volts	mA
1N957B	1N957B	6.46	6.8	7.14	18.5	4.5	700	1.0	150	5.2	47
1N958B	1N958B	7.125	7.5	7.875	16.5	5.5	700	0.5	75	5.7	42
1N959B	1N959B	7.79	8.2	8.61	15	6.5	700	0.5	50	6.2	38
1N960B	1N960B	8.645	9.1	9.555	14	7.5	700	0.5	25	6.9	35
1N961B	1N961B	9.5	10	10.5	12.5	8.5	700	0.25	10	7.6	32
1N962B	1N962B	10.45	11	11.55	11.5	9.5	700	0.25	5	8.4	28
1N963B	1N963B	11.4	12	12.6	10.5	11.5	700	0.25	5	9.1	26
1N964B	1N964B	12.35	13	13.65	9.5	13	700	0.25	5	9.9	24
1N965B	1N965B	14.25	15	15.75	8.5	16	700	0.25	5	11.4	21
1N966B	1N966B	15.2	16	16.8	7.8	17	700	0.25	5	12.2	19
1N967B	1N967B	17.1	18	18.9	7.0	21	750	0.25	5	13.7	17
1N968B	1N968B	19	20	21	6.2	25	750	0.25	5	15.2	15
1N969B	1N969B	20.9	22	23.1	5.6	29	750	0.25	5	16.7	14
1N970B	1N970B	22.8	24	25.2	5.2	33	750	0.25	5	18.2	13
1N971B	1N971B	25.65	27	28.35	4.6	41	750	0.25	5	20.6	11
1N972B	1N972B	28.5	30	31.5	4.2	49	1000	0.25	5	22.8	10
1N973B	1N973B	31.35	33	34.65	3.8	58	1000	0.25	5	25.1	9.2
1N974B	1N974B	34.2	36	37.8	3.4	70	1000	0.25	5	27.4	8.5
1N975B	1N975B	37.05	39	40.95	3.2	80	1000	0.25	5	29.7	7.8
1N978B	1N978B	48.45	51	53.55	2.5	125	1500	0.25	5	38.8	5.9
1N979B	1N979B	53.2	56	58.8	2.2	150	2000	0.25	5	42.6	5.4
1N982B	1N982B	71.25	75	78.75	1.7	270	2000	0.25	5	56	4.1

2. TOLERANCE AND VOLTAGE DESIGNATION

Tolerance designation – Device tolerance of $\pm 5\%$ is indicated by a "B" suffix.

3. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in the thermal equilibrium at the lead temperature (T_L) at 30°C \pm 1°C and 3/8″ lead length.

4. ZENER IMPEDANCE (Z_Z) DERIVATION

 Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_{Z(ac)} = 0.1 I_{Z(dc)}$ with the ac frequency = 60 Hz.

5. MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Values shown are based on the JEDEC rating of 400 mW where the actual zener voltage (V_Z) is known at the operating point, the maximum zener current may be increased and is limited by the derating curve.

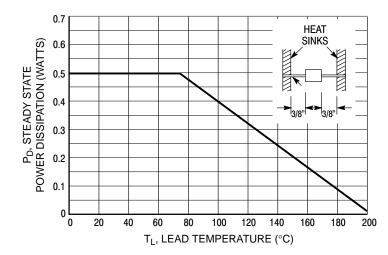


Figure 1. Steady State Power Derating

APPLICATION NOTE — ZENER VOLTAGE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$
.

 θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to 40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

$$\mathsf{T}_\mathsf{J} = \mathsf{T}_\mathsf{L} + \Delta \mathsf{T}_\mathsf{JL}.$$

 ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for dc power:

$$\Delta T_{JL} = \theta_{JL} P_D$$
.

For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta V = \theta_{VZ} T_{J}$$
.

 $\theta_{VZ}\!,$ the zener voltage temperature coefficient, is found from Figures 4 and 5.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 7. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 7 be exceeded.

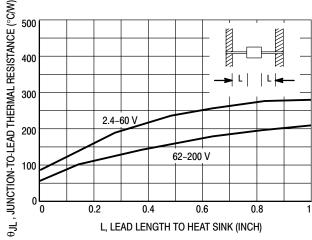


Figure 2. Typical Thermal Resistance

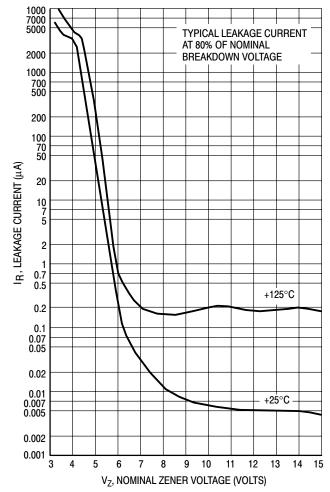
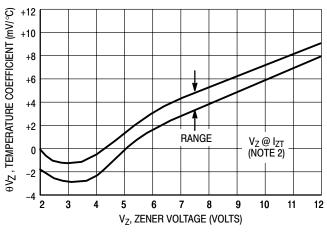


Figure 3. Typical Leakage Current

TEMPERATURE COEFFICIENTS

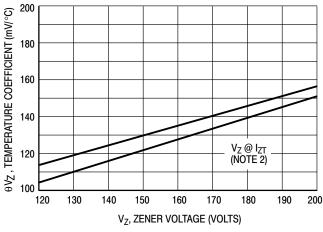
(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)



 $\theta V_{\mbox{\scriptsize Z}}$, TEMPERATURE COEFFICIENT (mV/ $^{\circ}\mbox{\scriptsize C})$ 70 50 30 20 Vz@ Iz (NOTE 2) 10 7 5 10 20 30 50 70 100 V₇, ZENER VOLTAGE (VOLTS)

Figure 4a. Range for Units to 12 Volts

Figure 4b. Range for Units 12 to 100 Volts



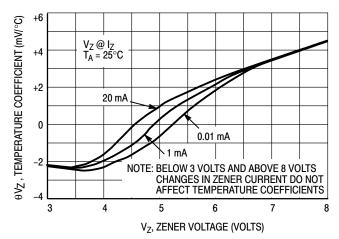
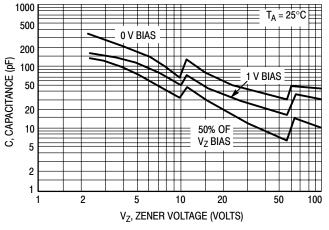


Figure 4c. Range for Units 120 to 200 Volts

Figure 5. Effect of Zener Current



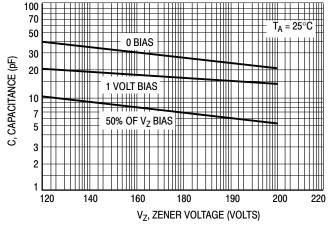


Figure 6a. Typical Capacitance 2.4-100 Volts

Figure 6b. Typical Capacitance 120-200 Volts

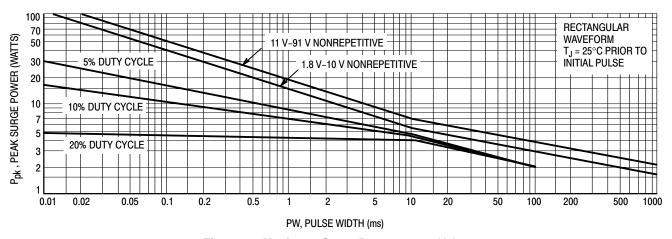


Figure 7a. Maximum Surge Power 1.8-91 Volts

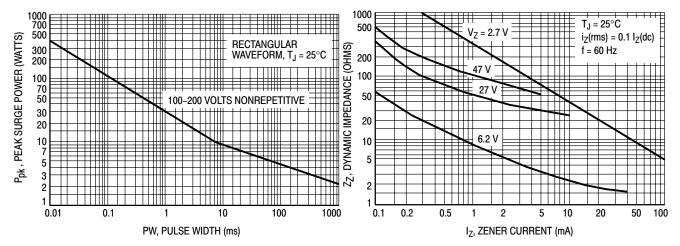


Figure 7b. Maximum Surge Power DO-204AH 100–200 Volts

Figure 8. Effect of Zener Current on Zener Impedance

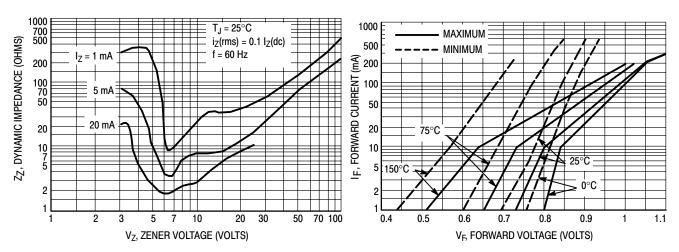


Figure 9. Effect of Zener Voltage on Zener Impedance

Figure 10. Typical Forward Characteristics

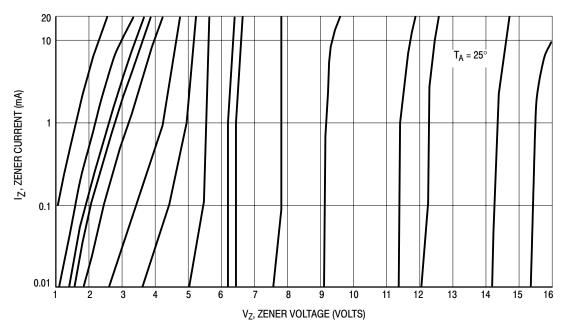


Figure 11. Zener Voltage versus Zener Current — $V_Z = 1$ thru 16 Volts

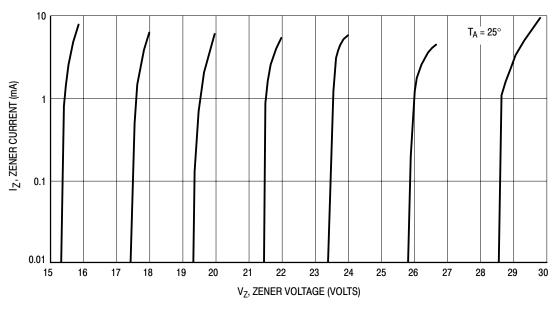


Figure 12. Zener Voltage versus Zener Current — V_Z = 15 thru 30 Volts

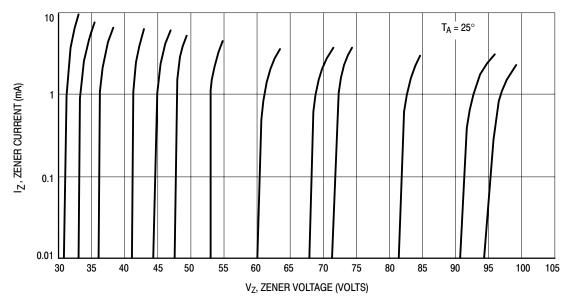


Figure 13. Zener Voltage versus Zener Current — $V_Z = 30$ thru 105 Volts

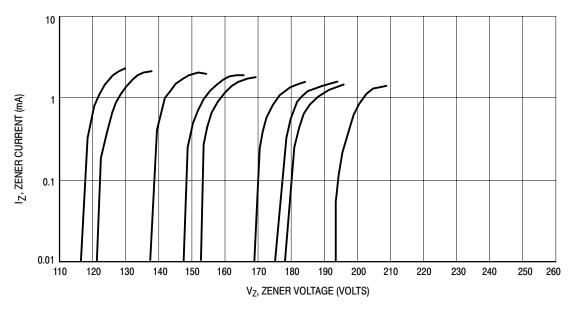


Figure 14. Zener Voltage versus Zener Current — V_Z = 110 thru 220 Volts

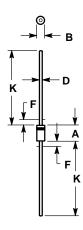
OUTLINE DIMENSIONS

Zener Voltage Regulators – Axial Leaded

500 mW DO-35 Glass

GLASS DO-35/D0-204AH

CASE 299-02 **ISSUE A**



- NOTES:

 1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.

 2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

 3. POLARITY DENOTED BY CATHODE BAND.
- 3. POLARITY DENOTED BY CATHODE BAND.
 4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	3.05	5.08	0.120	0.200	
В	1.52	2.29	0.060	0.090	
D	0.46	0.56	0.018	0.022	
F		1.27		0.050	
K	25.40	38.10	1.000	1.500	

All JEDEC dimensions and notes apply.





ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affliliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)

Email: ONlit-german@hibbertco.com

French Phone: (+1) 303–308–7141 (Mon–Fri 2:00pm to 7:00pm CET)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303–308–7142 (Mon–Fri 12:00pm to 5:00pm GMT)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

Toll-Free from Mexico: Dial 01-800-288-2872 for Access -

then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 1-303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031 **Phone**: 81–3–5740–2700

Email: r14525@onsemi.com

Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.